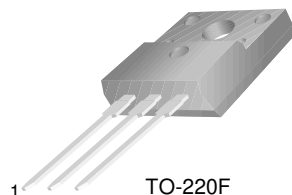


KSB1097

Low Frequency Power Amplifier

- Low Speed Switchng Industrial Use
- Complement to KSD1588



TO-220F
1.Base 2.Collector 3.Emitter

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	- 80	V
V_{CEO}	Collector-Emitter Voltage	- 60	V
V_{EBO}	Emitter-Base Voltage	- 7	V
I_C	Collector Current (DC)	- 7	A
I_{CP}	*Collector Current (Pulse)	- 15	A
I_B	Base Current	- 3.5	A
P_C	Collector Dissipation ($T_a=25^\circ\text{C}$)	2	W
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	30	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 55 ~ 150	$^\circ\text{C}$

* $PW \leq 300\mu\text{s}$, Duty Cycle $\leq 10\%$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
I_{CBO}	Collector Cut-off Current	$V_{CB} = - 60\text{V}$, $I_E = 0$		- 10	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = - 5\text{V}$, $I_C = 0$		- 10	μA
h_{FE1} h_{FE2}	* DC Current Gain	$V_{CE} = - 1\text{V}$, $I_C = - 3\text{A}$ $V_{CE} = - 1\text{V}$, $I_C = - 5\text{A}$	40 20	200	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = - 5\text{A}$, $I_B = - 0.5\text{A}$		- 0.5	V
$V_{BE(sat)}$	* Base-Emitter Saturation Voltage	$I_C = - 5\text{A}$, $I_B = - 0.5\text{A}$		- 1.5	V

* Pulse Test: $PW \leq 350\mu\text{s}$, Duty Cycle $\leq 2\%$ Pulsed

h_{FE} Classification

Classification	R	O	Y
h_{FE1}	40 ~ 80	60 ~ 120	100 ~ 200

Typical Characteristics

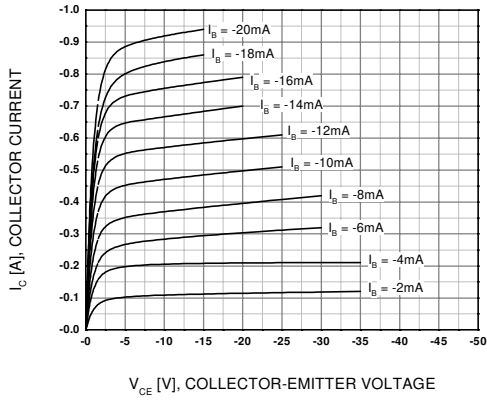


Figure 1. Static Characteristics

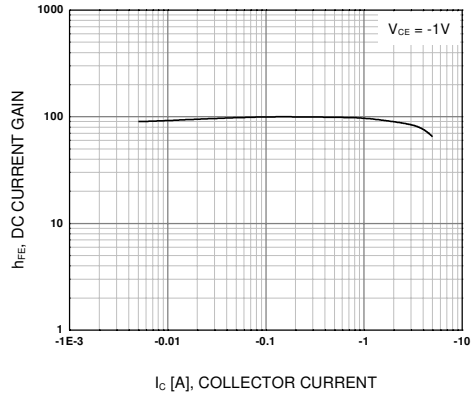


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

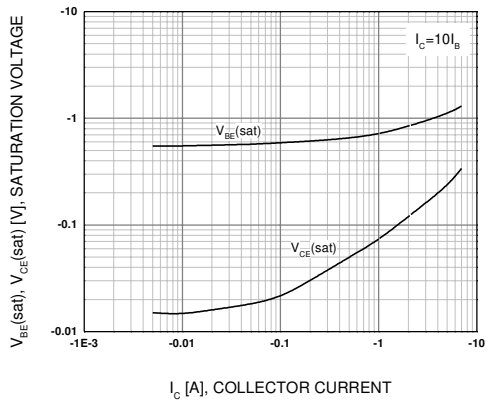


Figure 3. Saturation Voltage

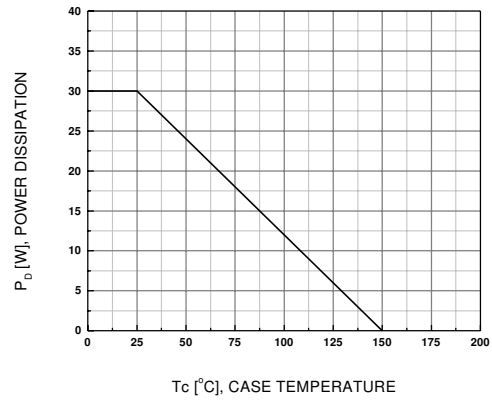


Figure 4. Power Derating

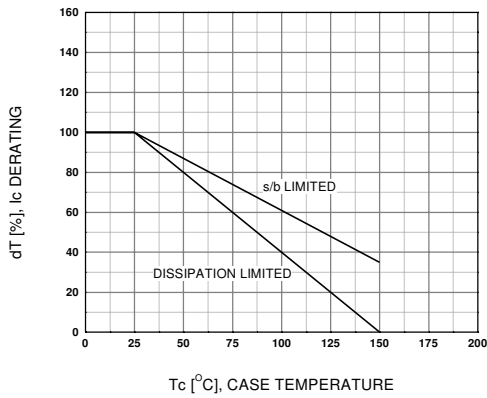


Figure 5. Power Derating

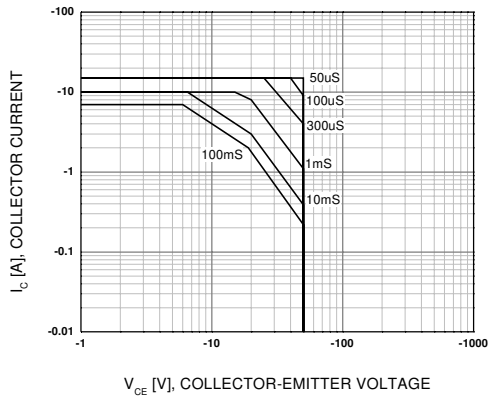
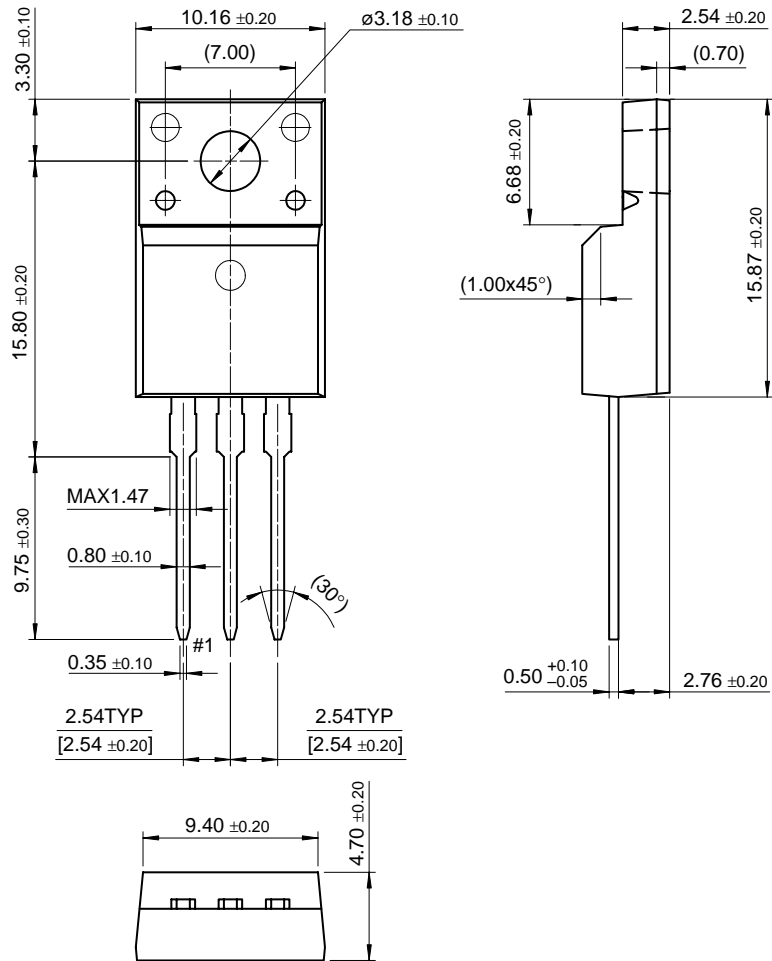


Figure 6. Safe Operating Area

Package Dimensions

KSB1097

TO-220F



Dimensions in Millimeters

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PNP Epitaxial Silicon Transistor

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Applications

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Product status/pricing/packageing

Product	Product status	Pricing*	Package type	Leads	Packing method
KSB1097YTU	Full Production	\$0.58	TO-220F	3	RAIL
KSB1097OTU	Full Production	\$0.58	TO-220F	3	RAIL
KSB1097RTU	Full Production	\$0.58	TO-220F	3	RAIL

* 1,000 piece Budgetary Pricing

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